

(@ T_C = 25℃ unless otherwise specified)

Forward voltage	I_D = 130A, Tvj = 25	V_F		1.20	1.40	V
Reverse leakage current	$V_R = V_{RRM}$, Tvj = 25	I_{RRM}			0.5	mA
	$V_R = V_{RRM}$, Tvj = 150				10	mA
Threshold voltage	For power loss calculation only Tvj = 150 ,	V_{TO}			0.87	V
Dynamic resistance		r_T			3.5	mΩ

(@ T_C = 25℃ unless otherwise specified)

Thermal impedance (junction to case)	per diode	$R_{th(j-c)}$			0.85	K/W
Mounting torque	Base plate to heatsink screw M6	M	4.25		5.75	N·m
	Electrode to terminal screw M6		4.25		5.75	N·m

JMD130TD20D2	JMD130TD20D2	D2	240g/PCS	2 PCS	24 PCS

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FIG.1: Forward characteristics(per diode)

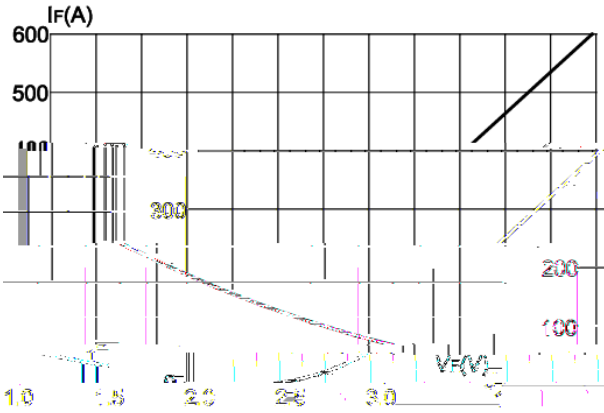
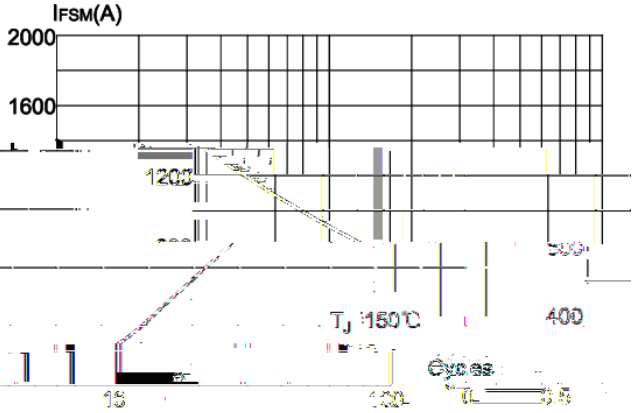
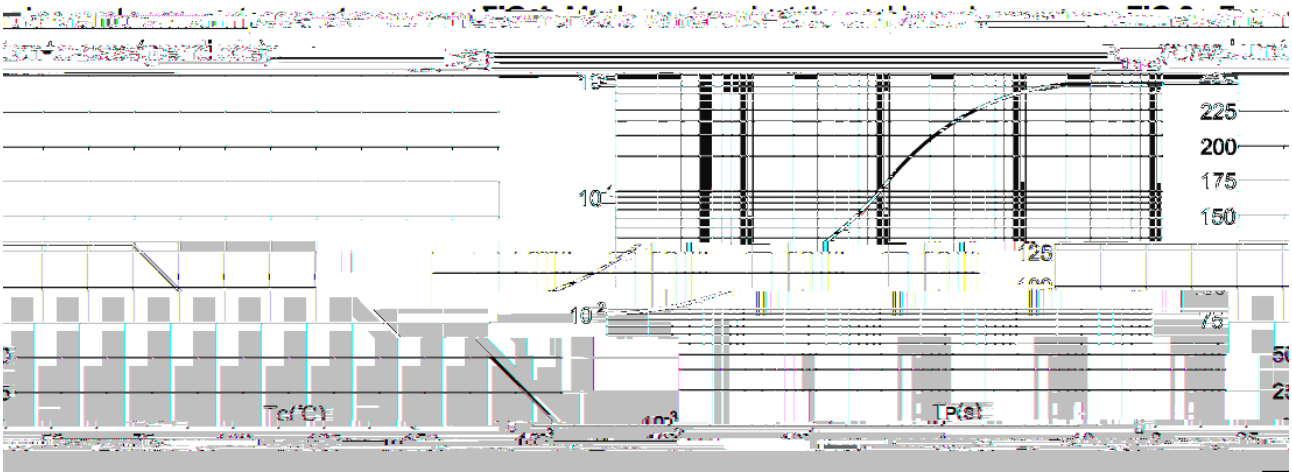
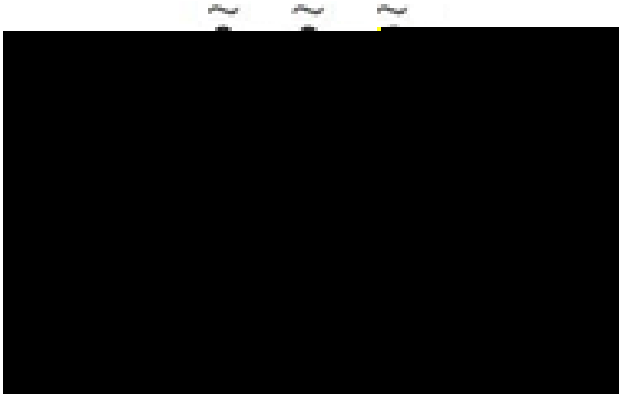


FIG.2: Peak on-state surge current







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